



FHD100

NPN Silicon Darlington High Power Transistor



Features:

1. Using triple-diffusion process.High output current. Small driving power.
2. Highest amplification factor. High inverse voltage.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for current output,voltage adjustment and servo circuit of numerical control machine.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications										Test Condition
			A	B	C	D	E	F	G	H	I	J	
Collector-Emitter Voltage	V _{CEO}	V	100	200	300	400	500	600	700	800	900	1000	
Emitter-Base Voltage	V _{EBO}	V	5										
Max. Collector Current	I _{CM}	A	10.0										
Max. Collector Dissipation	P _{CM}	W	100										T _c :75°C
Junction Temperature	T _{jm}	°C	175										
Storage Temperature	T _{stg}	°C	-55~+175										
Collector-Emitter Leakage Current	I _{CEO}	mA	Max.:1.0										V _{CE} =100V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	Max.:2.0										I _C =5A,I _B =0.1A
DC Current Gain	h _{FE}		Min.:500										V _{CE} =10V,I _C =5A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	100	200	300	400	500	600	700	800	900	1000	I _C =5mA
E-Base Breakdown Voltage	V _{(BR)EBO}	V	5										I _E =20mA

Outline and Dimensions: